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Team Nexperia



PNP resistor-equipped transistor; $R1 = 22 k\Omega$, $R2 = 22 k\Omega$ Rev. 2 — 4 May 2012 Product data s

Product data sheet

1. **Product profile**

1.1 General description

PNP Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTC124EMB.

1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs

1.3 Applications

- Low-current peripheral driver
- Control of IC inputs

- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Replaces general-purpose transistors in digital applications
- Mobile applications

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
lo	output current		-	-	-100	mA
R1	bias resistor 1 (input)	T _{amb} = 25 °C	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



PNP resistor-equipped transistor; R1 = 22 k Ω , R2 = 22 k Ω

2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)		
3	0	output (collector)	2 Transparent top view SOT883B (DFN1006B-3)	1 R1 R2 R2 R2 R2 R2 R2 R2 R2 R2 R2 R2 R2 R2

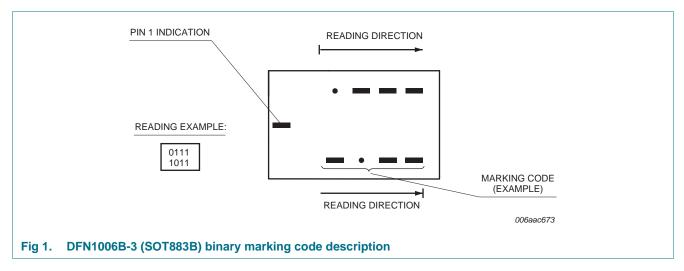
3. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PDTA124EMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B				

4. Marking

Table 4.	Marking	codes
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Type number	Marking code
PDTA124EMB	0010 0101



PNP resistor-equipped transistor; R1 = 22 k Ω , R2 = 22 k Ω

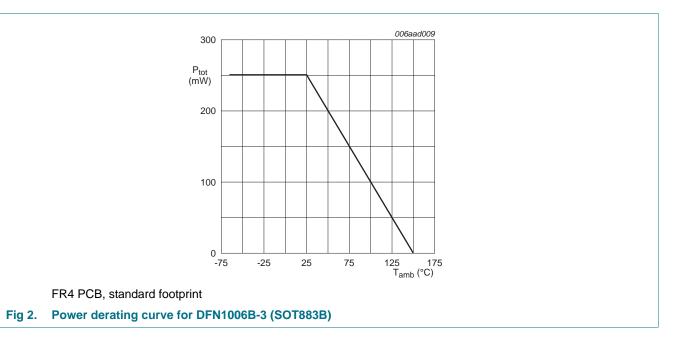
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-10	V
VI	input voltage	positive		-	10	V
		negative		-	-40	V
lo	output current			-	-100	mA
I _{CM}	peak collector current	pulsed; t _p ≤ 1 ms		-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u>	-	250	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

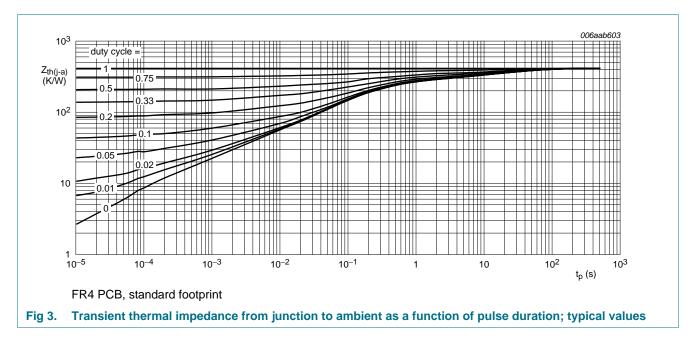


PNP resistor-equipped transistor; R1 = 22 k Ω , R2 = 22 k Ω

6. Thermal characteristics

Table 6.	. Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

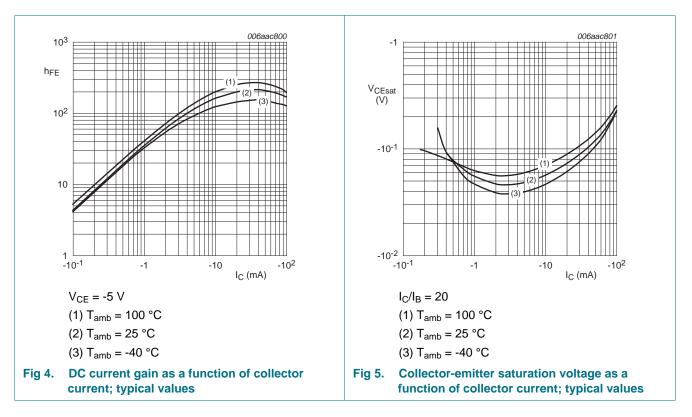


PNP resistor-equipped transistor; R1 = 22 k Ω , R2 = 22 k Ω

7. Characteristics

Characteristics					
Parameter	Conditions	Mir	тур	Max	Unit
collector-base cut-off current	V_{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
collector-emitter cut-off	V_{CE} = -30 V; I _B = 0 A; T _{amb} = 25 °C	-	-	-100	nA
current	V_{CE} = -30 V; I _B = 0 A; T _j = 150 °C	-	-	-5	μA
emitter-base cut-off current	V_{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-180	μΑ
DC current gain	V_{CE} = -5 V; I _C = -5 mA; T _{amb} = 25 °C	60	-	-	
collector-emitter saturation voltage	I_{C} = -10 mA; I_{B} = -0.5 mA; T_{amb} = 25 °C	-	-	-150	mV
off-state input voltage	V_{CE} = -5 V; I _C = -100 µA; T _{amb} = 25 °C	-	-1.1	-0.8	V
on-state input voltage	V_{CE} = -0.3 V; I _C = -5 mA; T _{amb} = 25 °C	-2.5	5 -1.7	-	V
bias resistor 1 (input)	T _{amb} = 25 °C	15.	4 22	28.6	kΩ
bias resistor ratio		0.8	1	1.2	
collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	3	pF
transition frequency	$V_{CE} = -5 \text{ V}; I_C = -10 \text{ mA}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	<u>11</u> -	180	-	MHz
	Parametercollector-base cut-off currentcollector-emitter cut-off currentemitter-base cut-off currentDC current gain collector-emitter saturation voltageoff-state input voltage on-state input voltagebias resistor 1 (input) bias resistor ratio collector capacitance	ParameterConditionscollector-base cut-off current $V_{CB} = -50 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ collector-emitter cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ witter-base cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_j = 150 \text{ °C}$ emitter-base cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ DC current gain $V_{CE} = -5 \text{ V}; \text{ I}_C = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ collector-emitter saturation voltage $I_C = -10 \text{ mA}; \text{ I}_B = -0.5 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ off-state input voltage $V_{CE} = -5 \text{ V}; \text{ I}_C = -100 \text{ µA}; \text{ T}_{amb} = 25 \text{ °C}$ on-state input voltage $V_{CE} = -0.3 \text{ V}; \text{ I}_C = -5 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ bias resistor 1 (input) $T_{amb} = 25 \text{ °C}$ bias resistor ratio $C_{CB} = -10 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ I}_e = 0 \text{ A}; _f = 1 \text{ MHz}; \text{ T}_{amb} = 25 \text{ °C}$ transition frequency $V_{CE} = -5 \text{ V}; \text{ I}_C = -10 \text{ mA}; \text{ f} = 100 \text{ MHz};$	ParameterConditionsMincollector-base cut-off current $V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ -collector-emitter cut-off current $V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ -collector-emitter cut-off current $V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}; T_j = 150 \text{ °C}$ -emitter-base cut-off current $V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ -DC current gain $V_{CE} = -5 \text{ V}; I_C = -5 \text{ mA}; T_{amb} = 25 \text{ °C}$ 60collector-emitter saturation voltage $I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$ -on-state input voltage $V_{CE} = -5 \text{ V}; I_C = -100 \text{ µA}; T_{amb} = 25 \text{ °C}$ -bias resistor 1 (input) $T_{amb} = 25 \text{ °C}$ 15.4bias resistor ratio $O.8$ 0.80.8collector capacitance $V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; I_B = 0 \text{ A}; I_B = 0 \text{ A}; I_C = -10 \text{ mA}; f = 100 \text{ MHz};$ 11f ansition frequency $V_{CE} = -5 \text{ V}; I_C = -10 \text{ mA}; f = 100 \text{ MHz};$ 11	ParameterConditionsMinTypcollector-base cut-off current $V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ collector-emitter cut-off current $V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ collector-emitter cut-off current $V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ emitter-base cut-off current $V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ DC current gain $V_{CE} = -5 \text{ V}; I_C = -5 \text{ mA}; T_{amb} = 25 \text{ °C}$ 60-collector-emitter saturation voltage $I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$ off-state input voltage $V_{CE} = -5 \text{ V}; I_C = -100 \text{ µA}; T_{amb} = 25 \text{ °C}$ on-state input voltage $V_{CE} = -5 \text{ V}; I_C = -5 \text{ mA}; T_{amb} = 25 \text{ °C}$ bias resistor 1 (input) $T_{amb} = 25 \text{ °C}$ 15.422bias resistor ratio0.81collector capacitance $V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$ transition frequency $V_{CE} = -5 \text{ V}; I_C = -10 \text{ mA}; f = 100 \text{ MHz};$ 11-180	$\begin{tabular}{ c c c c c c } \hline Parameter & Conditions & Min & Typ & Max \\ \hline collector-base cut-off current & V_{CB} = -50 V; I_E = 0 A; T_{amb} = 25 °C & - & - & -100 \\ \hline current & V_{CE} = -30 V; I_B = 0 A; T_{amb} = 25 °C & - & - & -100 \\ \hline current & V_{CE} = -30 V; I_B = 0 A; T_j = 150 °C & - & - & -55 \\ \hline emitter-base cut-off current & V_{EB} = -5 V; I_C = 0 A; T_{amb} = 25 °C & - & - & -55 \\ \hline emitter-base cut-off current & V_{CE} = -5 V; I_C = -5 mA; T_{amb} = 25 °C & - & - & -180 \\ \hline DC current gain & V_{CE} = -5 V; I_C = -5 mA; T_{amb} = 25 °C & - & - & -110 \\ \hline collector-emitter & I_C = -10 mA; I_B = -0.5 mA; T_{amb} = 25 °C & - & - & -1.1 & -0.8 \\ \hline off-state input voltage & V_{CE} = -5 V; I_C = -5 mA; T_{amb} = 25 °C & - & -1.1 & -0.8 \\ \hline on-state input voltage & V_{CE} = -5 V; I_C = -5 mA; T_{amb} = 25 °C & - & -1.1 & -0.8 \\ \hline on-state input voltage & V_{CE} = -0.3 V; I_C = -5 mA; T_{amb} = 25 °C & - & -1.1 & -0.8 \\ \hline on-state input voltage & V_{CE} = -0.3 V; I_C = -5 mA; T_{amb} = 25 °C & - & -1.1 & -0.8 \\ \hline on-state input voltage & V_{CE} = -10 V; I_E = 0 A; I_{amb} = 25 °C & - & -1.1 & -0.8 \\ \hline bias resistor 1 (input) & T_{amb} = 25 °C & - & -1.1 & -0.8 \\ \hline bias resistor ratio & V_{CB} = -10 V; I_E = 0 A; I_e = 0 A;$

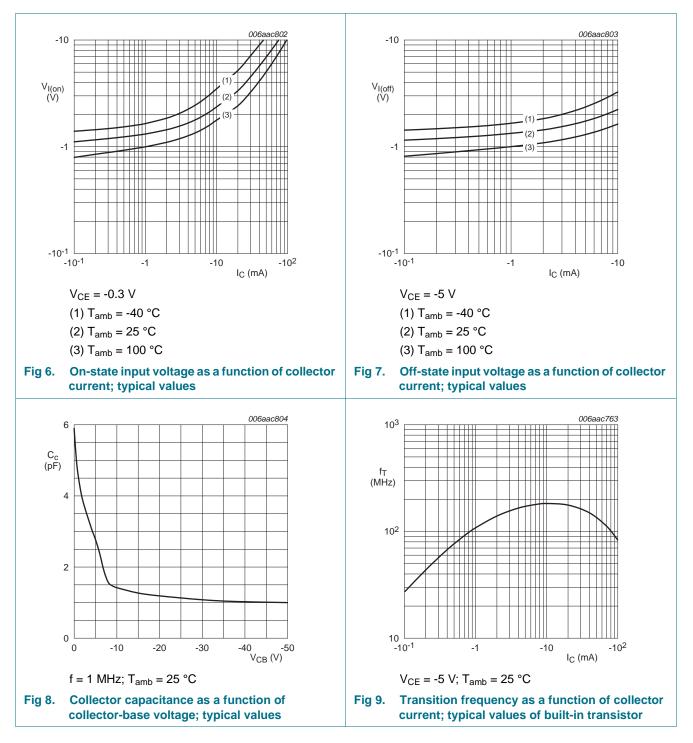
[1] Characteristics of built-in transistor.



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PNP resistor-equipped transistor; R1 = 22 k Ω , R2 = 22 k Ω



8. Test information

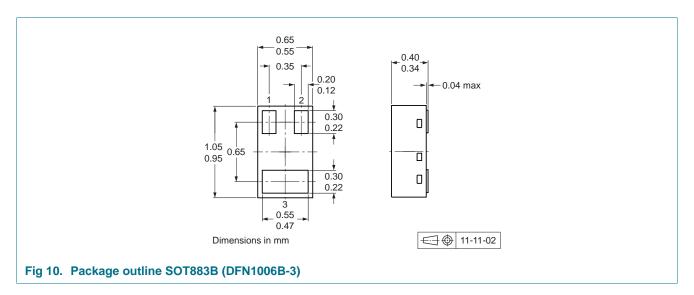
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

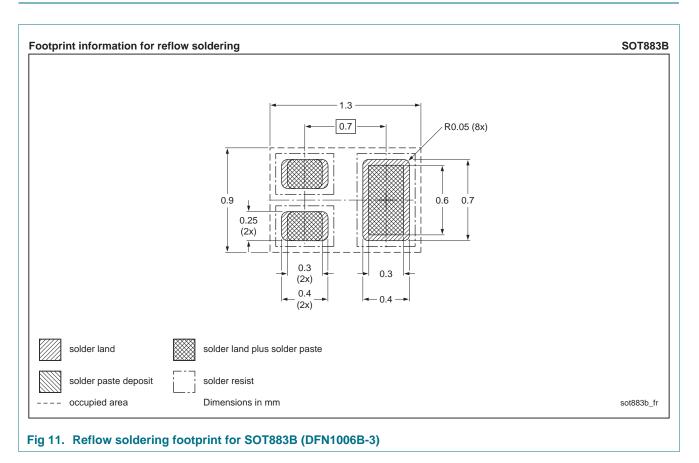
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PNP resistor-equipped transistor; R1 = 22 k Ω , R2 = 22 k Ω

9. Package outline



10. Soldering



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Rev. 2 — 4 May 2012

PNP resistor-equipped transistor; R1 = 22 k Ω , R2 = 22 k Ω

11. Revision history

Table 8.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTA124EMB v.2	20120504	Product data sheet	-	PDTA124EMB v.1
Modifications:	• 7 "Characterist	ics": parameter name corre	ected	
PDTA124EMB v.1	20120426	Product data sheet	-	-

PNP resistor-equipped transistor; R1 = 22 k Ω , R2 = 22 k Ω

12. Legal information

12.1 Data sheet status

Document status ^[1] ^[2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Product data sheet

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PNP resistor-equipped transistor; R1 = 22 k Ω , R2 = 22 k Ω

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